

isc Silicon NPN Power Transistor
2SD1405
DESCRIPTION

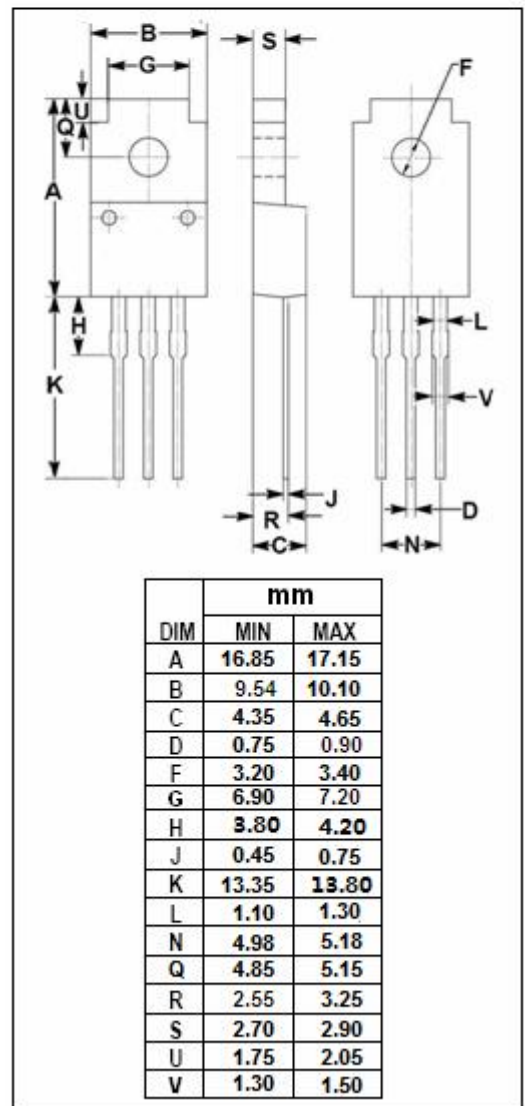
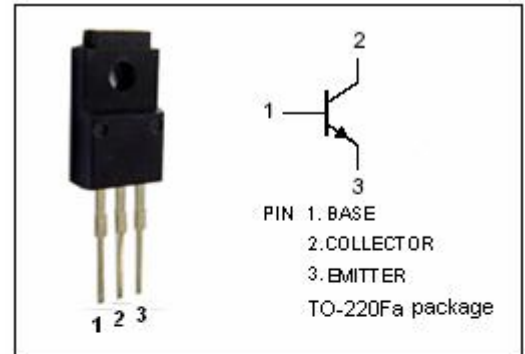
- High DC Current Gain
: $h_{FE} = 200(\text{Min}) @ I_C = 0.5\text{A}$
- Low Collector Saturation Voltage
: $V_{CE(\text{sat})} = 1.0\text{V}(\text{Max.}) @ I_C = 1\text{A}$
- Collector Power Dissipation of $25\text{W} @ T_C = 25^\circ\text{C}$
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

- Designed for audio frequency power amplifier applications.

ABSOLUTE MAXIMUM RATINGS ($T_a = 25^\circ\text{C}$)

| SYMBOL | PARAMETER | VALUE | UNIT |
|------------------|---|---------|------------------|
| V_{CBO} | Collector-Base Voltage | 50 | V |
| V_{CEO} | Collector-Emitter Voltage | 50 | V |
| V_{EBO} | Emitter-Base Voltage | 7 | V |
| I_C | Collector Current-Continuous | 3 | A |
| I_B | Base Current-Continuous | 0.5 | A |
| P_C | Collector Power Dissipation @ $T_C = 25^\circ\text{C}$ | 25 | W |
| T_J | Junction Temperature | 150 | $^\circ\text{C}$ |
| T_{stg} | Storage Temperature Range | -55~150 | $^\circ\text{C}$ |



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ELECTRICAL CHARACTERISTICS

 T_c=25°C unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | MIN | TYP. | MAX | UNIT |
|----------------------|--------------------------------------|--|-----|------|------|------|
| V _{(BR)CEO} | Collector-Emitter Breakdown Voltage | I _C = 50mA; I _B = 0 | 50 | | | V |
| V _{CE(sat)} | Collector-Emitter Saturation Voltage | I _C = 1A; I _B = 0.02A | | | 1.0 | V |
| V _{BE(on)} | Base -Emitter On Voltage | I _C = 0.5A; V _{CE} = 5V | | | 1.0 | V |
| I _{CBO} | Collector Cutoff Current | V _{CB} = 50V; I _E = 0 | | | 100 | μ A |
| I _{EBO} | Emitter Cutoff Current | V _{EB} = 7V; I _C = 0 | | | 100 | μ A |
| h _{FE} | DC Current Gain | I _C = 0.5A; V _{CE} = 5V | 200 | | 1200 | |
| C _{OB} | Output Capacitance | I _E = 0; V _{CB} = 10V; f _{test} =1MHz | | 70 | | pF |
| f _T | Current-Gain—Bandwidth Product | I _E = -0.5A; V _{CE} = 5V | | 5 | | MHz |

Switching times

| | | | | | | |
|------------------|--------------|--|--|-----|--|-----|
| t _{on} | Turn-on Time | I _{B1} =10mA; I _{B2} = 20mA, V _{CC} = 10V | | 2.0 | | μ s |
| t _{stg} | Storage Time | | | 5.0 | | μ s |
| t _f | Fall Time | | | 3.0 | | μ s |

h_{FE} Classifications

| GR | BL | V |
|---------|---------|----------|
| 200-400 | 350-700 | 600-1200 |

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